

Supplemental information for: Universal sublinear resistivity in vanadium kagome materials hosting charge density waves

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S1. POWDER X-RAY DIFFRACTION

Powder X-Ray Diffraction measurements were performed on ground acid-etched crystals in a Panalytical Empyrean diffractometer with Cu K_α X-ray source. Refinement with FullProf [1], Figs. S1 (a) and (b), revealed that ScV₆Sn₆ and LuV₆Sn₆ have a $P6/mmm$ HfFe₆Ge₆-type structure of the sample.

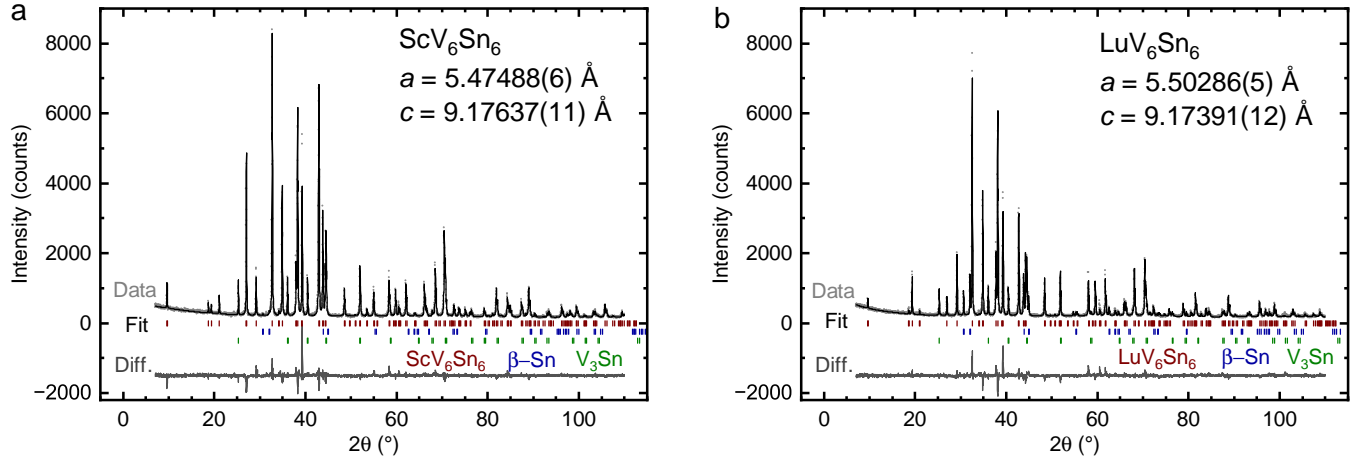


FIG. S1. Powder x-ray diffraction refinement of crushed (a) ScV₆Sn₆ and (b) LuV₆Sn₆ single crystals using Cu K_α radiation.

S2. SIMULTANEOUS FITTING OF THE MAGNETORESISTIVITY AND HALL RESISTANCE TO THE TWO-BAND MODEL

We fitted the in-plane magnetoresistivity and Hall resistivity to the simple two-band model [2, 3] through Eq. S1:

$$\begin{aligned} \rho_{xx} &= \frac{1}{e} \frac{(n_h \mu_h + n_e \mu_e) + (n_h \mu_e + n_e \mu_h) \mu_h \mu_e B^2}{(n_h \mu_h + n_e \mu_e)^2 + (n_h - n_e)^2 \mu_h^2 \mu_e^2 B^2} \\ \rho_{xy} &= \frac{B}{e} \frac{(n_h \mu_h^2 - n_e \mu_e^2) + (n_h - n_e) \mu_h^2 \mu_e^2 B^2}{(n_h \mu_h + n_e \mu_e)^2 + (n_h - n_e)^2 \mu_h^2 \mu_e^2 B^2} \end{aligned} \quad (\text{S1})$$

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where n_e and n_h are the carrier densities for electrons and holes, respectively, and μ_e and μ_h are their corresponding mobilities. The results of simultaneous fitting of the in-plane magnetoresistance (MR_{xx}) and Hall resistivity (ρ_{yx}) to Eq. S1 are shown in Fig. S2. Charge carrier densities and mobilities as a function of temperature are shown in Fig. S3. At low temperatures for ScV_6Sn_6 , the simultaneous fitting of MR_{xx} and ρ_{yx} to Eq. S1 is not quite successful

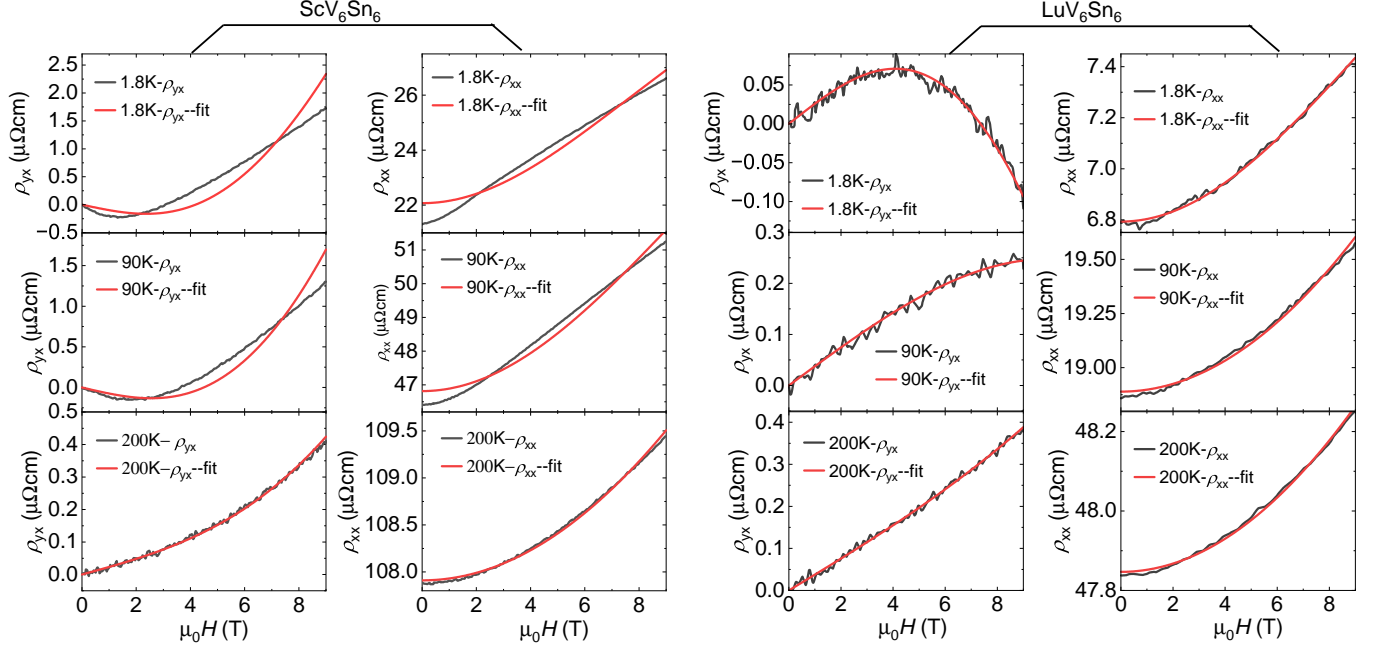


FIG. S2. Black lines are the longitudinal resistivity ρ_{xx} and Hall resistance ρ_{yx} for ScV_6Sn_6 and LuV_6Sn_6 as a function of magnetic field μ_0H and for several temperatures. Red lines are the best obtained curves from the simultaneous fitting of ρ_{xx} and ρ_{yx} to the two-band model [see Eq. S1].

(Fig. S2) due to the sublinear dependence of the magnetoresistance on the field. Note that the two-band model predicts a parabolic behavior for the magnetoresistance as a function of the field. Nevertheless, we report the values we obtained for n and μ since the modeling can capture the overall behavior of MR_{xx} and ρ_{yx} .

S3. HALL CONDUCTIVITY

Hall conductivity for current along the a axis (in-plane Hall conductivity) was calculated via the relation $\sigma_{yx} = -\rho_{yx}/(\rho_{xx}\rho_{yy} + \rho_{yx}^2)$. Hall conductivity for current along the c axis (out-of-plane Hall conductivity) was calculated via the relation $\sigma_{yz} = -\rho_{yz}/(\rho_{yy}\rho_{zz} + \rho_{yz}^2)$.

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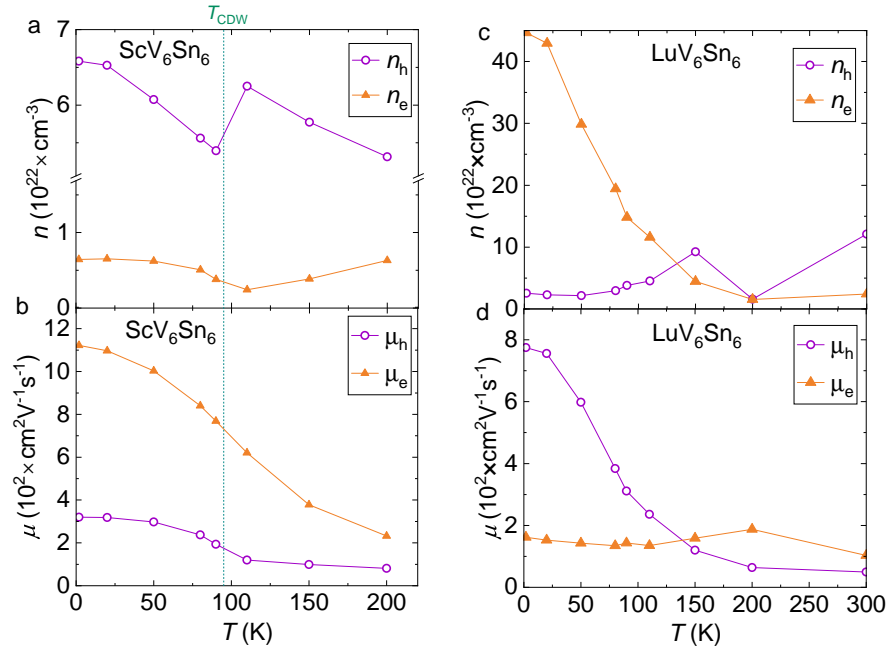


FIG. S3. Summary of two band model fits of $\rho_{xx}(H)$ and $\rho_{yx}(H)$ for ScV₆Sn₆ and LuV₆Sn₆. (a) Charge carrier densities and (b) mobilities for ScV₆Sn₆. (c) Charge carrier densities and (d) mobilities for LuV₆Sn₆. n_e (n_h) and μ_e (μ_h) are density and mobility for electrons (holes).

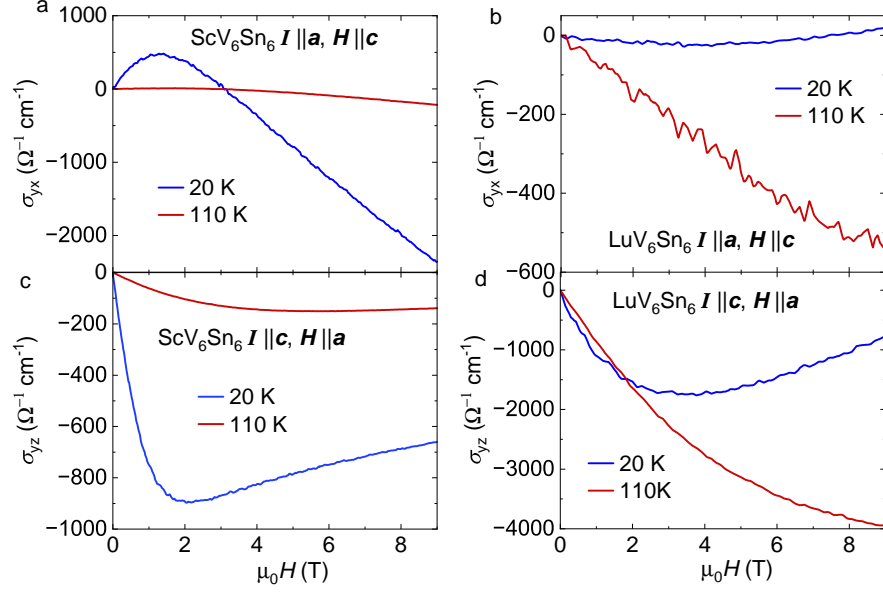


FIG. S4. In-plane (σ_{yx}) and out-of-plane (σ_{yz}) Hall conductivity for ScV₆Sn₆ and LuV₆Sn₆ above and below T_{CDW} .